

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number: PMBT5401,235
Manufacturer: NXP USA Inc.
Package: TO-236-3, SC-59, SOT-23-3
Availability: Please confirm with sales

Product Page:

<https://antrexco.com/product/details/nxp-usa-inc/pmbt5401-235.html>

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Contact Information

Email: info@antrexco.com

WhatsApp: +86-186-8066-5326

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Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

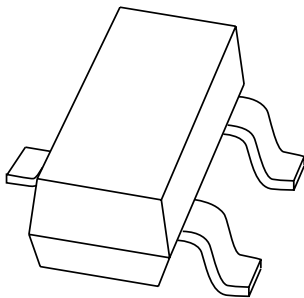
Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

DATA SHEET



PMBT5401 PNP high-voltage transistor

Product specification
Supersedes data of 1999 Apr 15

2004 Jan 21

PNP high-voltage transistor

PMBT5401

FEATURES

- Low current (max. 300 mA)
- High voltage (max. 150 V).

APPLICATIONS

- Switching and amplification in high voltage applications such as telephony.

DESCRIPTION

PNP high-voltage transistor in a SOT23 plastic package.
NPN complement: PMBT5550.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBT5401	*2L

Note

- * = p : Made in Hong Kong.
* = t : Made in Malaysia.
* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

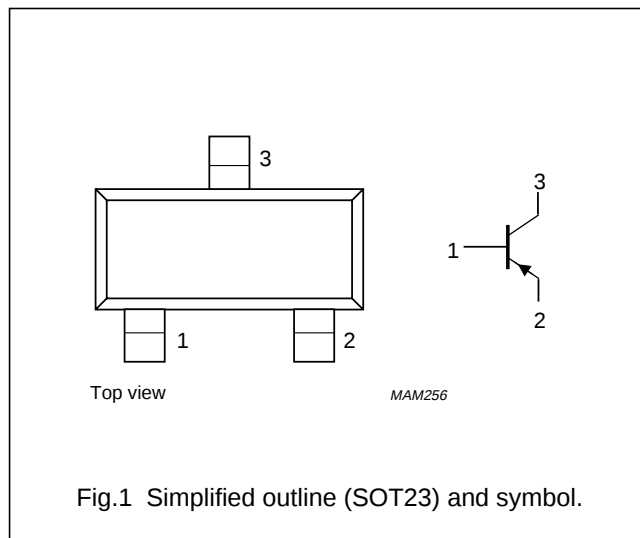


Fig.1 Simplified outline (SOT23) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMBT5401	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–160	V
V_{CEO}	collector-emitter voltage	open base	–	–150	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–300	mA
I_{CM}	peak collector current		–	–600	mA
I_{BM}	peak base current		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

PNP high-voltage transistor

PMBT5401

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

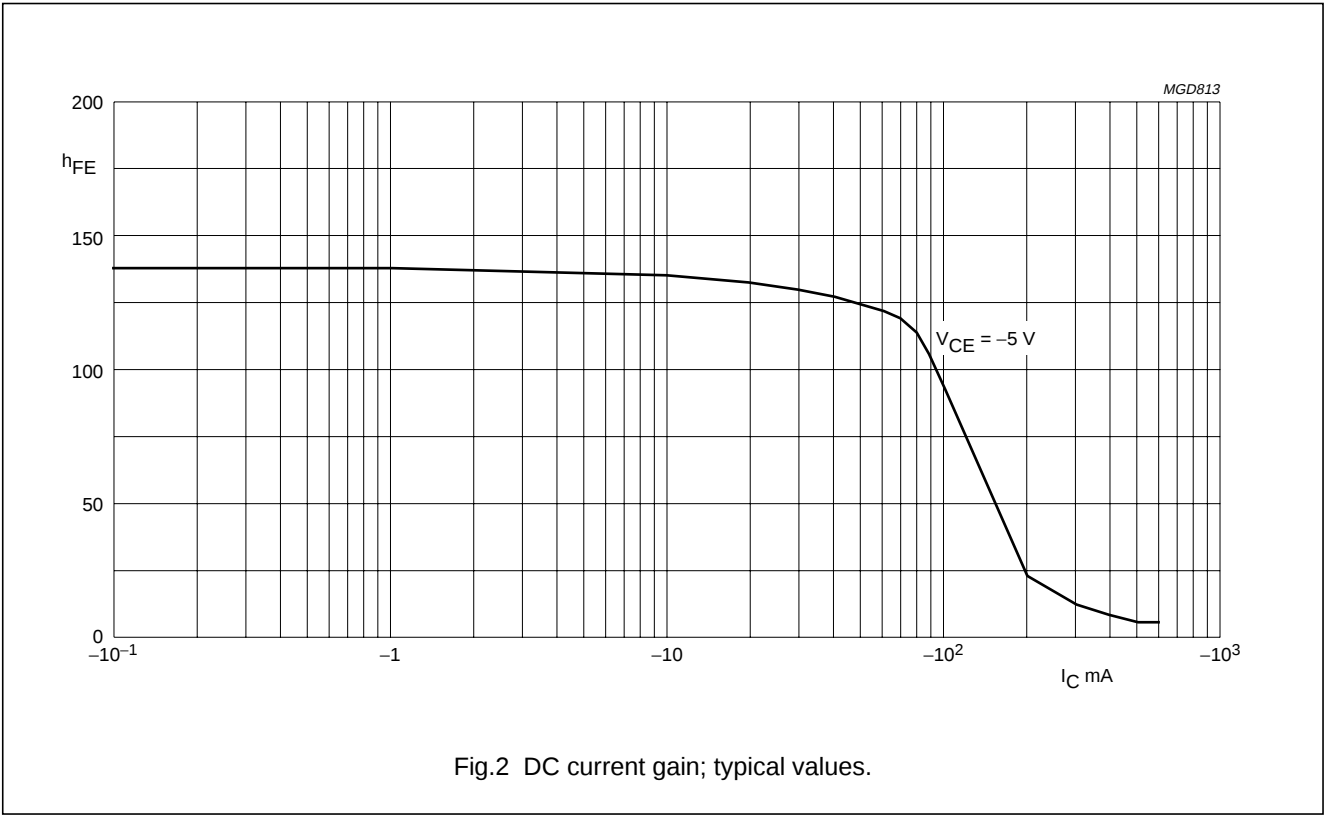
CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$I_E = 0; V_{CB} = -120\text{ V}$	–	–50	nA
		$I_E = 0; V_{CB} = -120\text{ V}; T_{amb} = 150\text{ °C}$	–	–50	μA
I_{EBO}	emitter-base cut-off current	$I_C = 0; V_{EB} = -4\text{ V}$	–	–50	nA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V};$ (see Fig.2)			
		$I_C = -1\text{ mA}$	50	–	
		$I_C = -10\text{ mA}$	60	240	
		$I_C = -50\text{ mA}$	50	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$	–	–200	mV
		$I_C = -50\text{ mA}; I_B = -5\text{ mA}$	–	–500	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$	–	–1	V
		$I_C = -50\text{ mA}; I_B = -5\text{ mA}$	–	–1	V
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	6	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -10\text{ V};$ $f = 100\text{ MHz}; T_{amb} = 25\text{ °C}$	100	300	MHz
F	noise figure	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 10\text{ Hz to }15.7\text{ kHz}; T_{amb} = 25\text{ °C}$	–	8	dB

PNP high-voltage transistor

PMBT5401



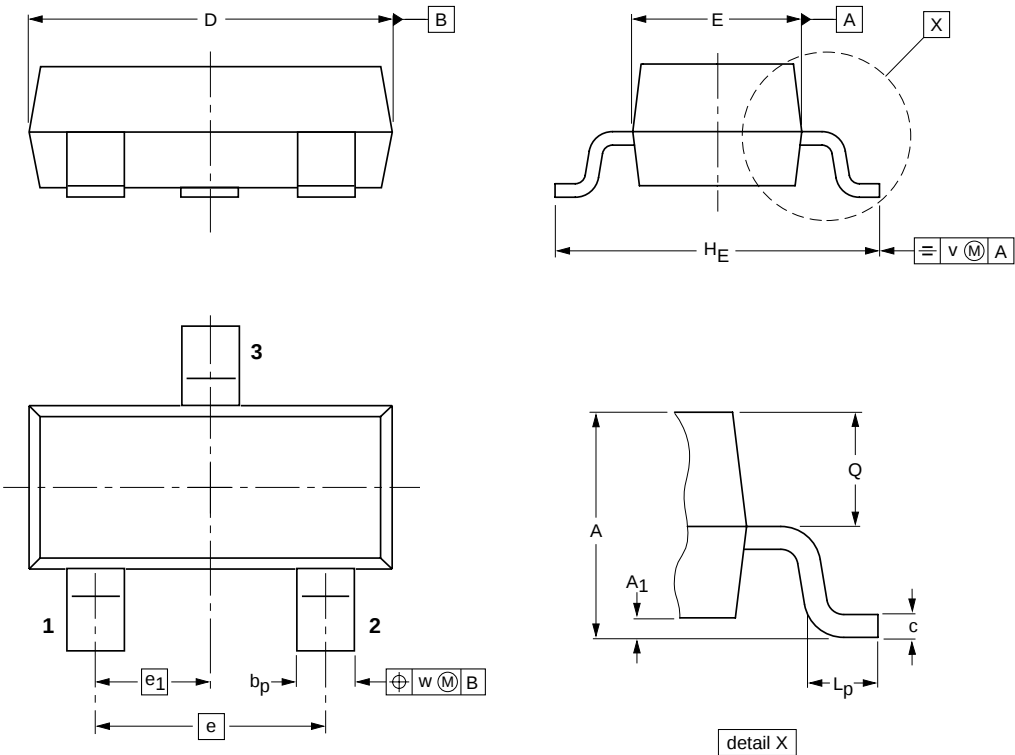
PNP high-voltage transistor

PMBT5401

PACKAGE OUTLINE

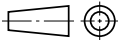
Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28 99-09-13

PNP high-voltage transistor

PMBT5401

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Notes

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3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Contact information

For additional information please visit <http://www.semiconductors.philips.com>. Fax: **+31 40 27 24825**

For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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